

Silicon NPN Power Transistors

BDX65

DESCRIPTION

- With TO-3 package
- DARLINGTON
- Complement to type BDX64

APPLICATIONS

- Designed for power amplification and switching applications.

PINNING (See Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

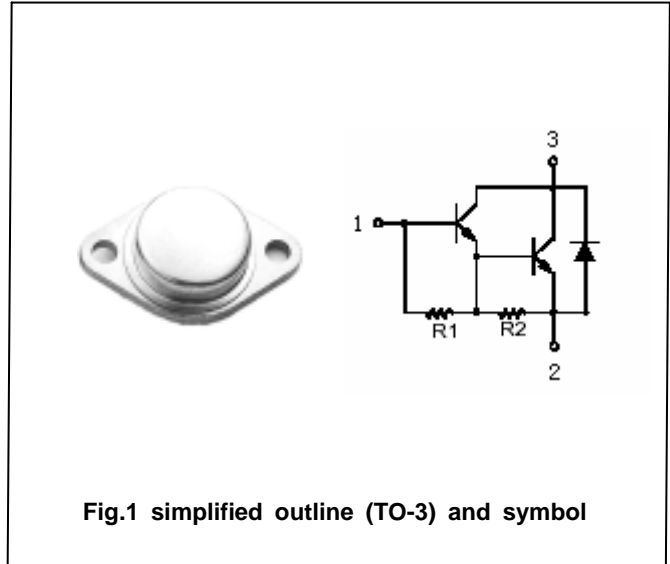


Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings(Ta=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	80	V
V _{CEO}	Collector-emitter voltage	Open base	60	V
V _{EBO}	Emitter-base voltage	Open collector	5	V
I _C	Collector current		12	A
I _{CM}	Collector current(peak)		16	A
I _B	Base current		0.2	A
P _T	Total power dissipation	T _C =25	117	W
T _j	Junction temperature		-55~200	
T _{stg}	Storage temperature		-55~200	

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal resistance from junction to case	1.5	/W

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEQ(SUS)}	Collector-emitter sustaining voltage	I _C =0.1A ; I _B =0;L=25mH	60			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =5A ; I _B =20mA			2	V
V _{BE}	Base-emitter voltage	I _C =5A;V _{CE} =3V			3	V
I _{CBO}	Collector cut-off current	V _{CB} =60V; I _E =0 T _C =150			0.4 3	mA
I _{CEO}	Collector cut-off current	V _{CE} =30V; I _B =0			1	mA
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			5	mA
V _F	Diode forward voltage	I _F =3A		1.8		V
h _{FE-1}	DC current gain	I _C =1A ; V _{CE} =3V		1500		
h _{FE-2}	DC current gain	I _C =5A ; V _{CE} =3V	1000			
h _{FE-3}	DC current gain	I _C =10A ; V _{CE} =3V		1500		
f _T	Transition frequency	I _C =5A ; V _{CE} =3V;f=1MHz		7		MHz

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PACKAGE OUTLINE

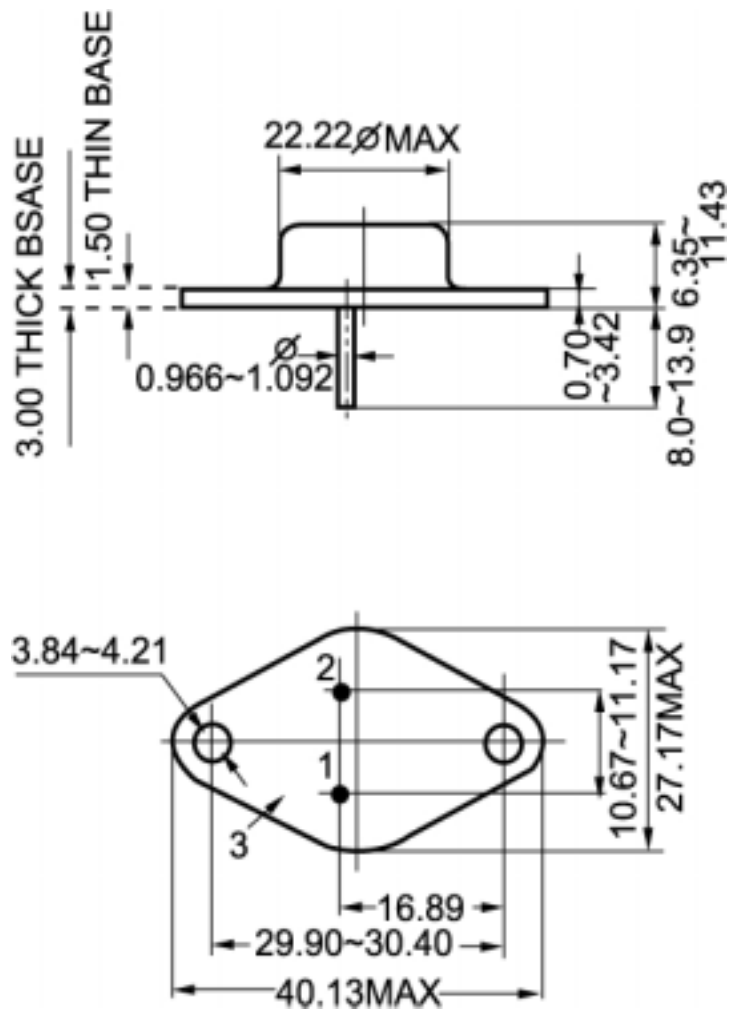


Fig.2 Outline dimensions